

Amendments To The Specification

Please substitute the following amended paragraph 17 for the original paragraph 17 on page 4 of the Specification.

[17] An n-type semiconductor layer 40 is coupled to the base 32. A buried collector 42, constructed from an enhanced n-type semiconductor layer, or an N⁺ type semiconductor, is coupled to a collector contact 44 and the n-type semiconductor layer 40. Openings are left in an insulating layer 46 for contact to the underlying semiconductor material. Although it is preferable to have a buried collector 42, an HBT may be constructed without a buried collector 42. In this case, the n-type semiconductor layer 40 acts as a collector and would be coupled to the base 32 and the collector contact 44. As illustrated in FIG. 1, this embodiment of a heterojunction bipolar transistor (HBT) 30 is an n-type device, because the emitter is an n-type semiconductor, the base is a p-type semiconductor, and the collector is an n-type semiconductor.